Preliminary

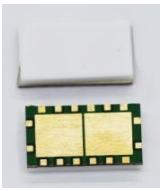
GaN Hybrid PAM SDM23005-30H

Product Features

- 2300~2400MHz
- 70.8W Saturated Power @ 48V
- 13% Drain Efficiency @ 33dBm
- Internally 50ohm Matched
- 2-Stage Amplifier Module
- GaN on SiC Technology

Applications

- Massive MIMO
- 4G System
- Multi-Band, Multi-Mode
- Multi-Carrier
- RRH Drive Amplifier



Package Type : PP-3G

Description

The SDM23005-30H is a fully integrated micro-strip GaN Hybrid power amplifier module designed for applications in 4G LTE MIMO systems, small cells and low power remote radio heads. SDM Series is an integrated 2-stage power amplifier module, 50ohm input and output impedance matched device can deliver up to 70.8W of saturation power and operating drain voltage 48V. This device is size 8x14x2.6mm and is packaged in a ceramic surface mount package.

Typical Performance

(V_{DS}= +48V, T_C=25℃, 50Ω)

Frequency [MHz]	Peak Power	Average Power*1			
	Power [W]	Power [W]	Gain [dB]	Drain Efficiency [%]	ACLR [dBc]
2310	61.8	2.0	42.1	12.7	-41.2
2350	59.2	2.0	41.9	13.0	-41.8
2390	59.2	2.0	41.3	13.2	-43.0

Note

*1 Measured in the SDM23005-30H test board amplifier circuit, under LTE 20MHz 1carrier, PAR 7.5dB @0.01% probability on CCDF.

Absolute Maximum Ratings

Rating	Symbol	Value	Unit	Condition
Drain to Source Voltage	V_{DSS}	100	V	Tc=25℃
Gate to Source Voltage	V_{GS}	-10, +2	V	Tc=25℃
Operating Voltage	V_{DD}	52	V_{DC}	
Storage Temperature	T_{STG}	-40, +125	℃	
Case Operating Temperature	T_C	-30, +125	℃	
Operating Junction Temperature*1	T_J	225	℃	
Soldering Temperature*2	T_S	250	℃	

Note

*1 Continuous use at maximum temperature will affect MTTF.

*2 Refer to the Application Note(AN-002) on soldering - "Solder Condition for RFHIC's GaN Device"

Electrical Characteristics[*1] (T_C=25℃ unless otherwise noted)

Characteristics	Conditions	Symbol	Min	Typ	Max	Unit
DC Characteristics (Main)						
Maximum Forward Gate Current	**Tc= 25℃**	I_{GMAX}	-	-	8	mA
Maximum Drain Current[*2]	**Tc= 25℃**	I_{DMAX}	-	-	4.76	A
Power Dissipation	**Tc= 85℃**	P_{DMAX}	-	-	41.2	W
Gate Threshold Voltage	**V_{DS} = 10V** **I_D = 7.8mA**	$V_{GS(TH)}$	-3.8	-3.0	-2.3	V_{DC}
Gate Quiescent Voltage	**V_{DS} = 48V** **I_D = 120mA**	$V_{GS(Q)}$	-3.7	-2.9	-2.2	V_{DC}
Drain-Source Breakdown Voltage	**V_{GS} = -8V** **I_D = 7.8mA**	V_{BR}	150	-	-	V
Saturated Drain Current[*3]	**V_{DS} = 6V** **V_{GS} = 2V**	I_{DS}	6.3	7.8	-	A
Gate Leakage Current	**V_{GS} = -8V** **V_{DS} = 150V**	$I_{GLKG150}$	-2.4	-	-	mA
Drain Leakage Current	**V_{GS} = -8V** **V_{DS} = 150V**	$I_{DLKG150}$	-	-	3.1	mA
DC Characteristics (Drive)						
Maximum Forward Gate Current	**Tc= 25℃**	I_{GMAX}	-	-	2	mA
Maximum Drain Current[*2]	**Tc= 25℃**	I_{DMAX}	-	-	0.8	A
Power Dissipation	**Tc= 85℃**	P_{DMAX}	-	-	21.2	W
Gate Threshold Voltage	**V_{DS} = 10V** **I_D = 2.16mA**	$V_{GS(TH)}$	-3.8	-3.0	-2.3	V_{DC}
Gate Quiescent Voltage	**V_{DS} = 48V** **I_D = 40mA**	$V_{GS(Q)}$	-3.7	-2.9	-2.2	V_{DC}
Drain-Source Breakdown Voltage	**V_{GS} = -8V** **I_D = 2.16mA**	V_{BR}	150	-	-	V
Saturated Drain Current[*3]	**V_{DS} = 6V** **V_{GS} = 2V**	I_{DS}	1.7	2.1	-	A
Gate Leakage Current	**V_{GS} = -8V** **V_{DS} = 150V**	$I_{GLKG150}$	-0.7	-	-	mA
Drain Leakage Current	**V_{GS} = -8V** **V_{DS} = 150V**	$I_{DLKG150}$	-	-	0.9	mA

Note

*1 Measured on wafer prior to packaging.

*2 Current Limit for long term, reliable operation

*3 Scaled from PCM data.

Characteristics	Conditions	Symbol	Min	Typ	Max	Unit
RF Characteristics (F=2350MHz unless otherwise noted)						
Saturated Output Power[*1, 4]	V_{DS} = 48V	P_{SAT}	56	70.8	100	W
Modulated Gain[*2]	V_{DS} = 48V P_{OUT} = 33dBm	G_P	40	41	45	dB
Linearity[*2]	V_{DS} = 48V P_{OUT} = 33dBm	ACLR	-50	-40	-33	dBc
Modulated Drain Efficiency[*2]	V_{DS} = 48V P_{OUT} = 33dBm	η	10	13	16	%
Output Mismatch Stress[*1, 3]	V_{DS} = 48V P_{OUT} = P_{SAT} Pulsed	VSWR	-	-	10:1	ψ

Note

*1 Pulse width 10μsec, Pulse period 100μsec.

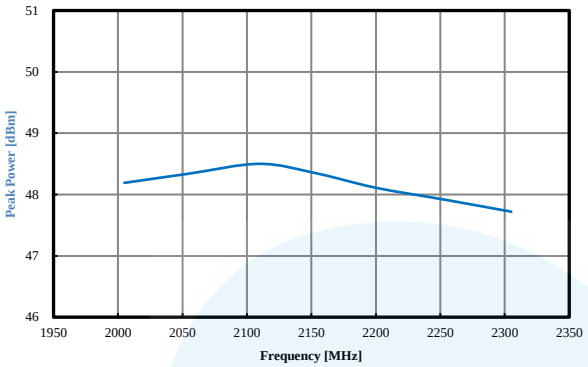
*2 Measured in the SDM23005-30H test board amplifier circuit, under LTE 20MHz 1carrier, PAR 7.5dB @0.01% probability on CCDF.
Drive Idq=40mA, Main Idq=120mA

*3 Measured in the SDM23005-30H test board amplifier circuit. No damage at all phase angles.

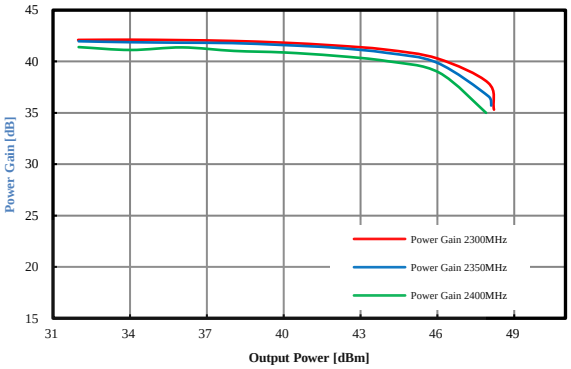
*4 Psat is defined as ΔPout/ΔPin<0.1, where ΔPin is increased input power, ΔPout is increased output power.

Typical Pulsed Signal Performance (Tc=25℃, Measured in the SDM23005-30H test board amplifier circuit)

Peak Power vs. Frequency



Pulsed Power Gain vs. Output Power

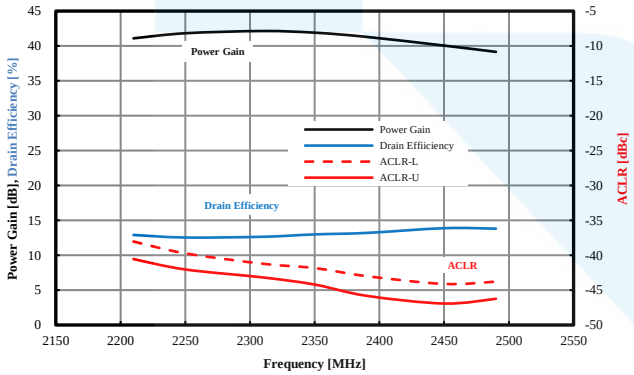


V_{DS} = 48V, Drive Idq=40mA, Main Idq=120mA

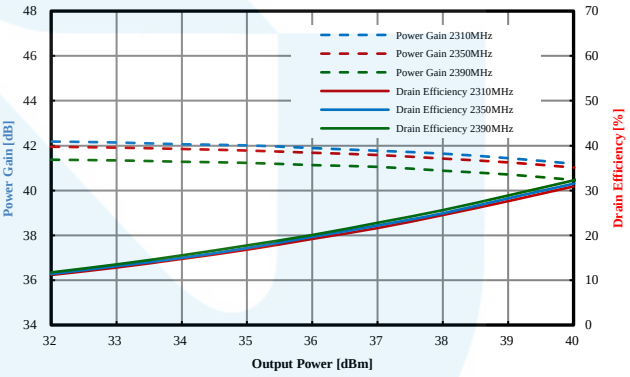
Pulse width 100µsec, Pulse period 1ms

Typical Modulated Signal Performance (Tc=25℃, Measured in the SDM23005-30H test board amplifier circuit)

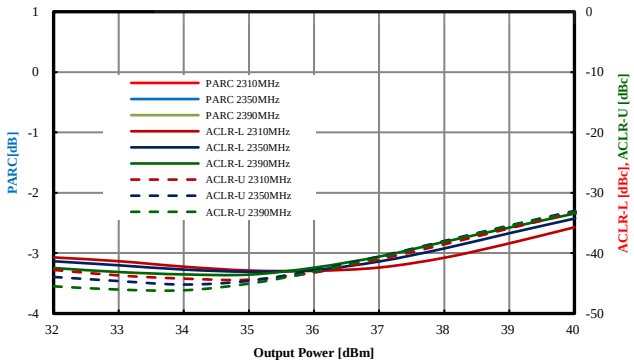
Power Gain, Drain Efficiency, ACLR vs. Frequency



Power Gain, Drain Efficiency vs. Output Power



PARC, ACLR vs. Output Power

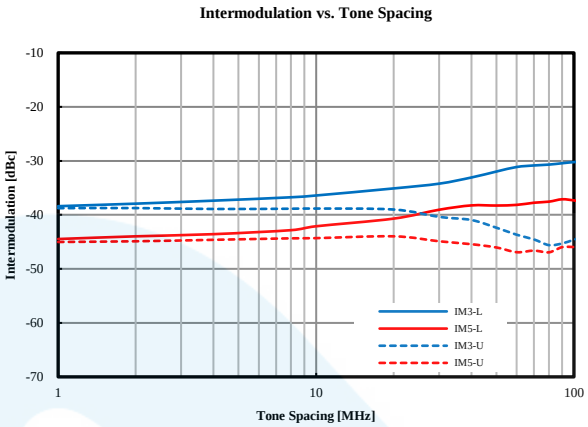


V_{DS} = 48V, Drive Idq=40mA, Main Idq=120mA

LTE 20MHz 1carrier, PAR 7.5dB @0.01% probability on CCDF.

Typical 2-tone Intermodulation Imbalance Performance

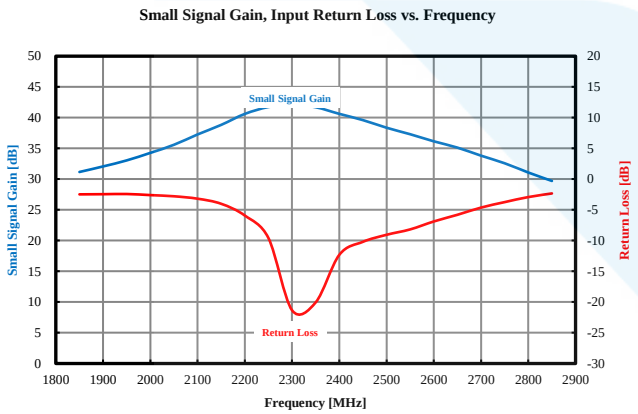
(Tc=25°C, Measured in the SDM23005-30H test board amplifier circuit)

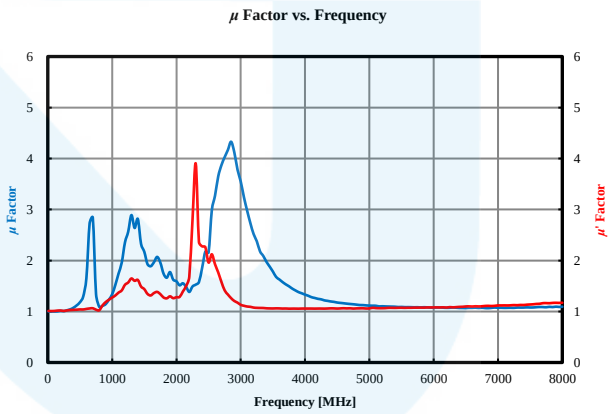


2-tone Power = 33dBm, V_{DS} = 48V, Drive Idq=40mA, Main Idq=120mA

Typical Small Signal Performance

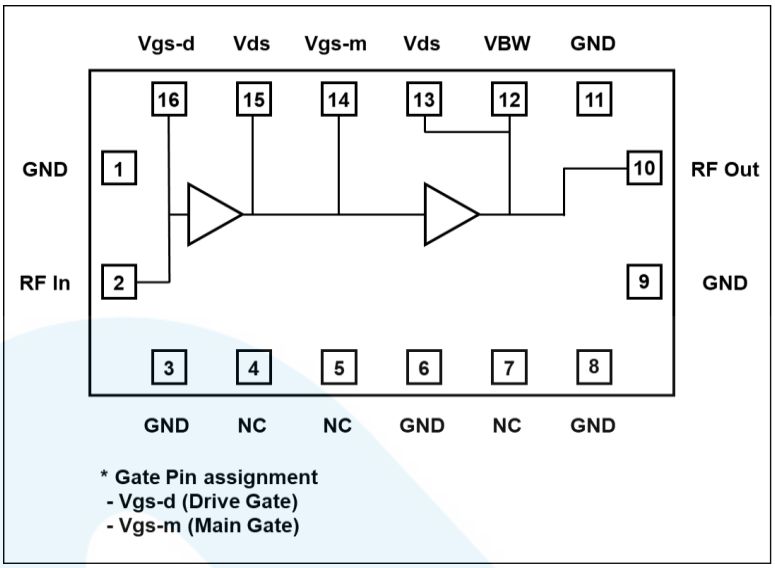
(Tc=25°C, Measured in the SDM23005-30H test board amplifier circuit)



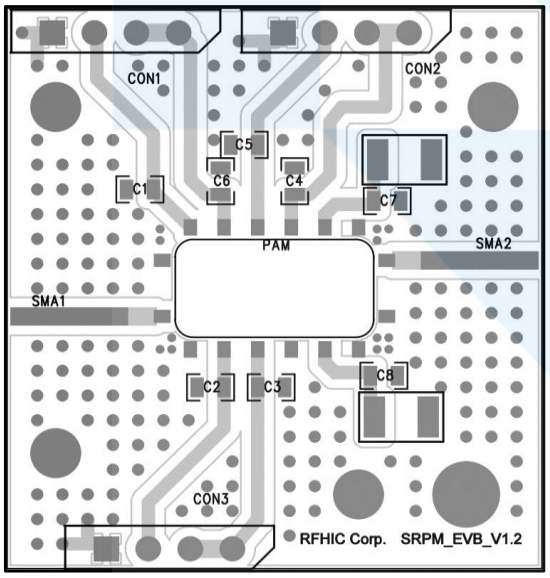


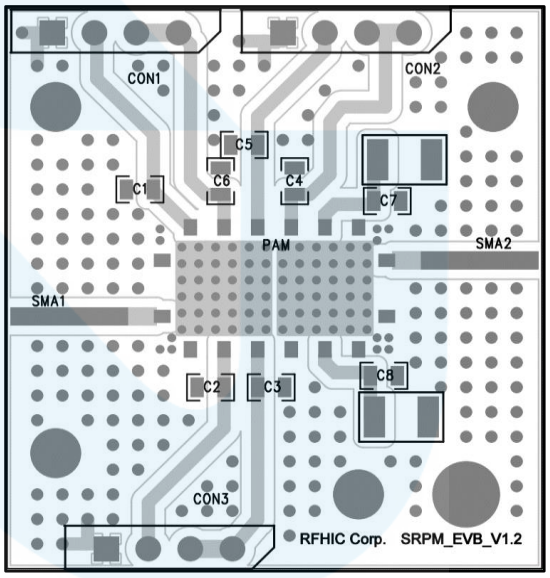
Input Power= -20dBm, V_{DS} = 48V, Drive Idq=40mA, Main Idq=120mA

Block Diagram



Test Board Component Layout with Coin Embedded and Thermal Via Type

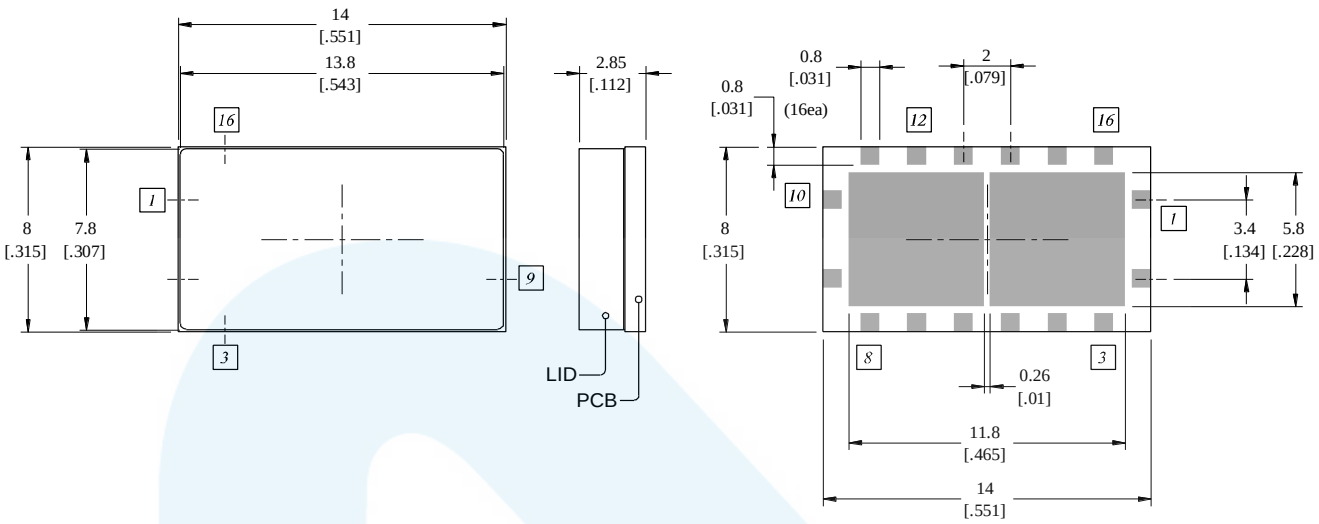




Part	Description	Part Number	Manufacturer
C4, C6, C7	1.0uF / 100V	GRM21BC72A105KE01	MURATA
C1, C5	4.7uF / 16V	TAJA475M016RNJ	AVX
PCB	2Layer, 20mil, 1oz	RO4350B	ROGERS
CON1~2	2.54mm Male Connector	5267-04A	MOLEX
SMA1~2	Female Connector	-	-
PAM	GaN Hybrid PAM	SDM23005-30H	RFHIC

Package Dimensions (Type:PP-3G)

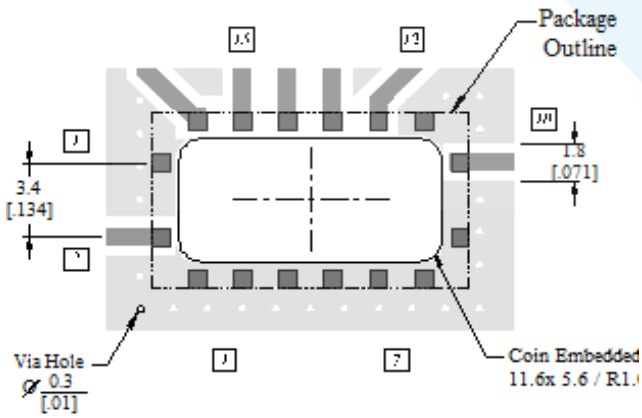
* Unit: mm[inch] | Tolerance: ±0.15[.006]



Pin Description								
2	4	5	10	13	14	15	16	12
RF In	-	-	RF Out	V_{DS}	V_{GS-m}	V_{DS}	V_{GS-d}	VBW
-	-	-	-	Main	Main	Drive	Drive	

* Other Pins are GND.

Recommended Footprint & Coin Embedded



Revision History

Part Number	Release Date	Version	Description	Data Sheet Status
SDM23005-30H	March. 2024	0.1	Initial version	Preliminary

Certification

This product is manufactured by a company that is certified for the AS9100D quality management system.